



Light collection and simulation in

nEXO 

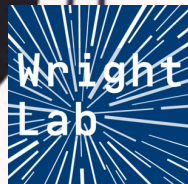
Molly Watts

Yale University

CPAD Workshop | RDC2: Photodetectors

November 8, 2023

Image: Symmetry magazine

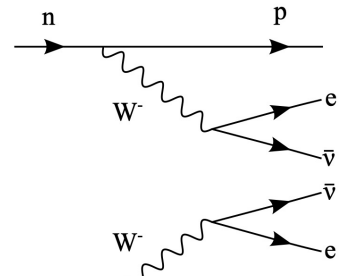


Neutrinoless double beta decay ($0\nu\beta\beta$)

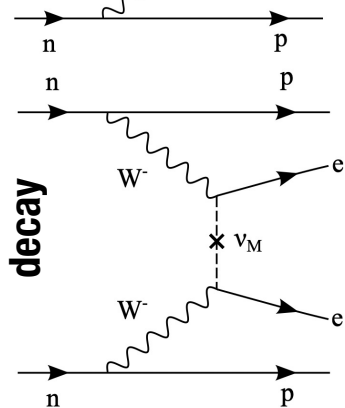
Finding $0\nu\beta\beta$ implies physics beyond the Standard Model

1. Lepton number violation

Double beta decay



Neutrinoless double beta decay



2. New class of elementary particles

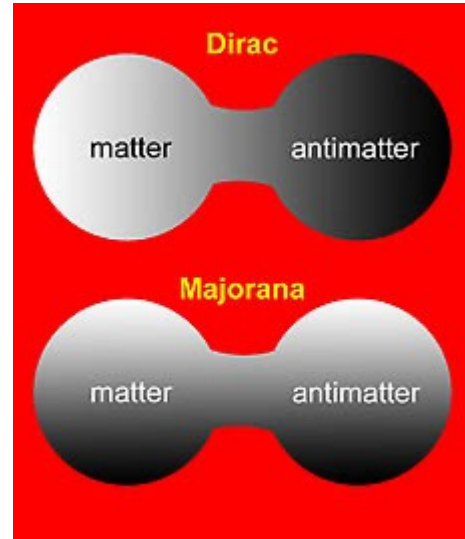


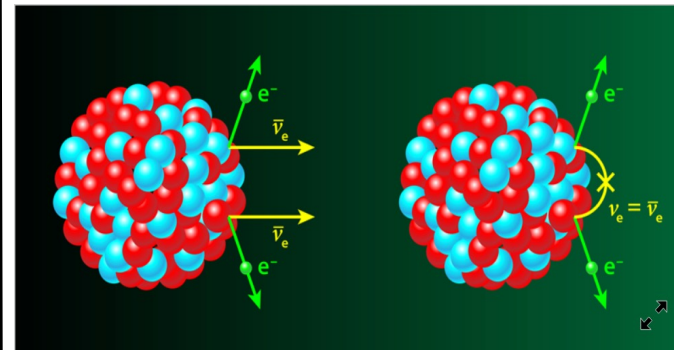
Image: Fermilab Today

Neutrinos are Majorana particles

$$\nu = \bar{\nu}$$

3. Implications for matter-antimatter asymmetry

Image: APS/ Alan Stonebraker



Double beta decay

Leptons & Anti-leptons

Neutrinoless double beta decay

Only leptons

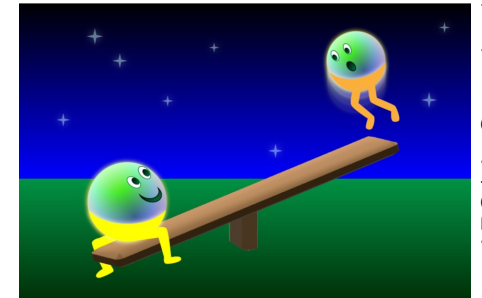
4. Insight into neutrino mass

$T_{1/2}$ - neutrino mass relationship

$$(T_{1/2})^{-1} \sim |\langle m_{\beta\beta} \rangle|^2$$

&

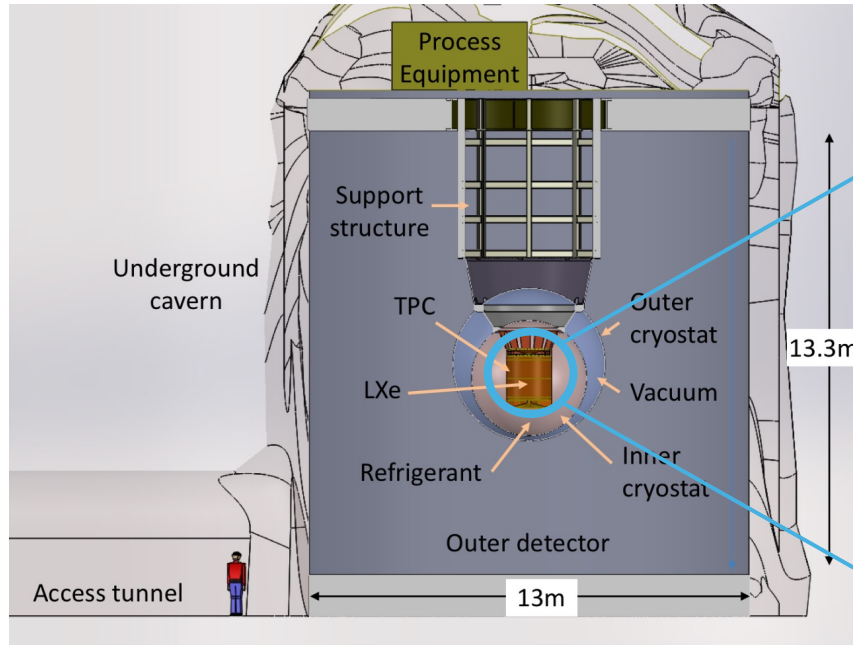
Possible new mass giving mechanism



See-saw mechanism

Image: APS/ A. Stonebraker

nEXO Planned $0\nu\beta\beta$ detector



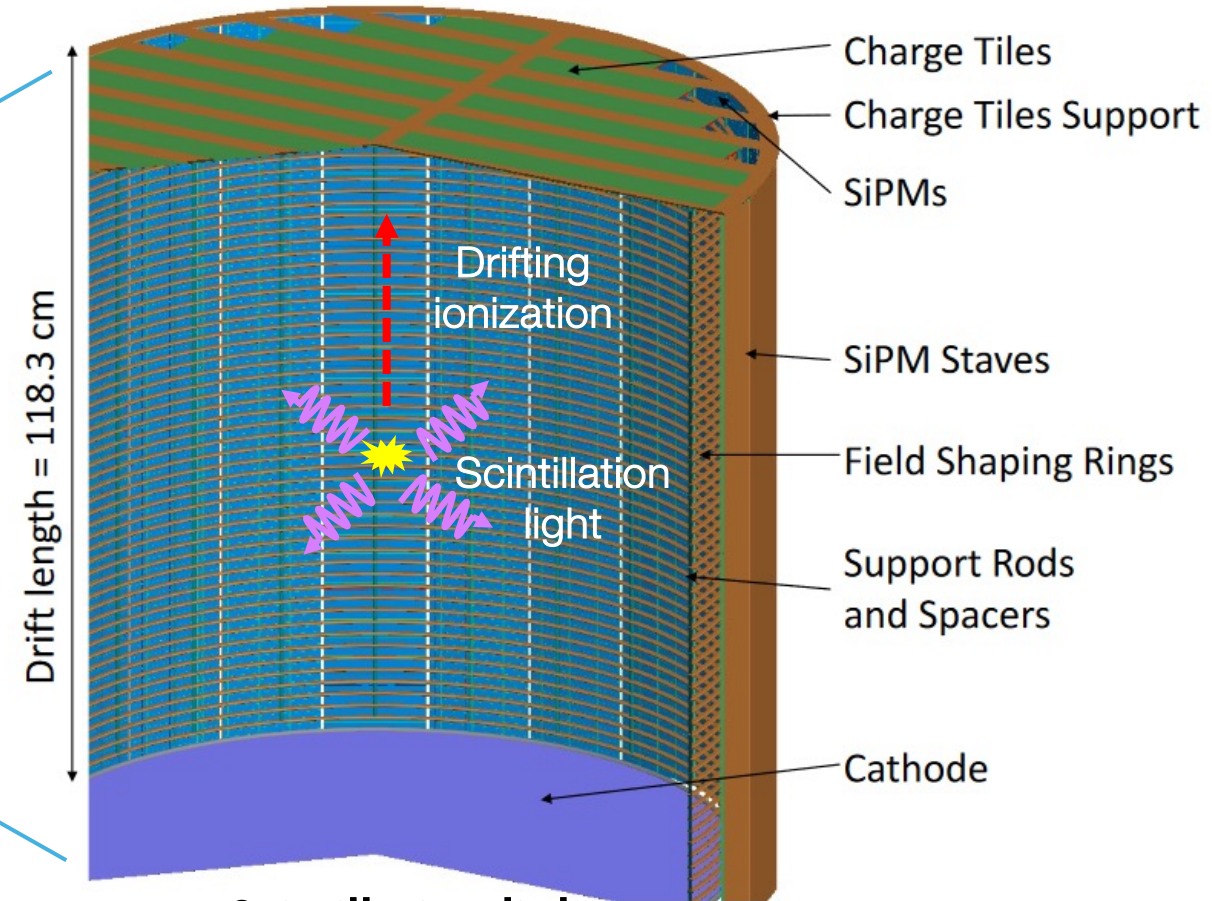
Builds off success of EXO-200
1st observation of $2\nu\beta\beta$ in ^{136}Xe

Single phase TPC

400 V/cm drift field, ~1.2 m drift length

5,000 kg of LXe enriched to 90% ^{136}Xe
High Q-value of 2458 keV

Detector size exceeds gamma ray absorption length
Self shielding, Scalability



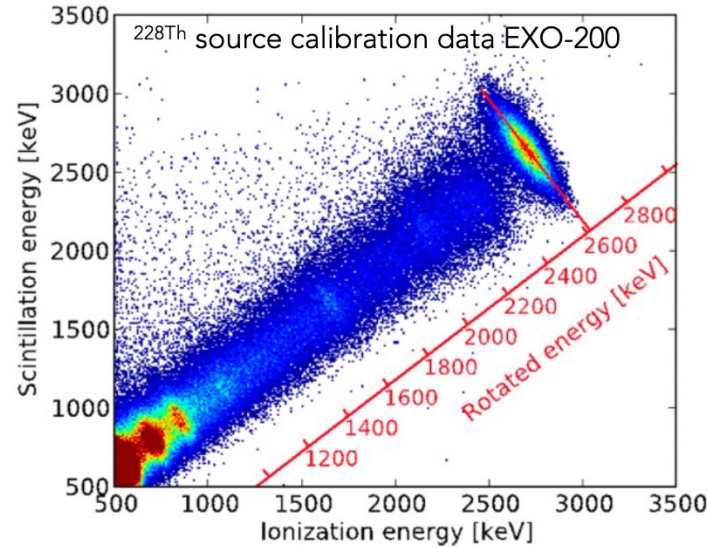
Scintillation light

- Time stamp of interaction time
- Independent measurement of charge and light is instrumental for energy resolution requirement of $\leq 1.1\%$ and our energy resolution goal of $\leq 0.8\%$

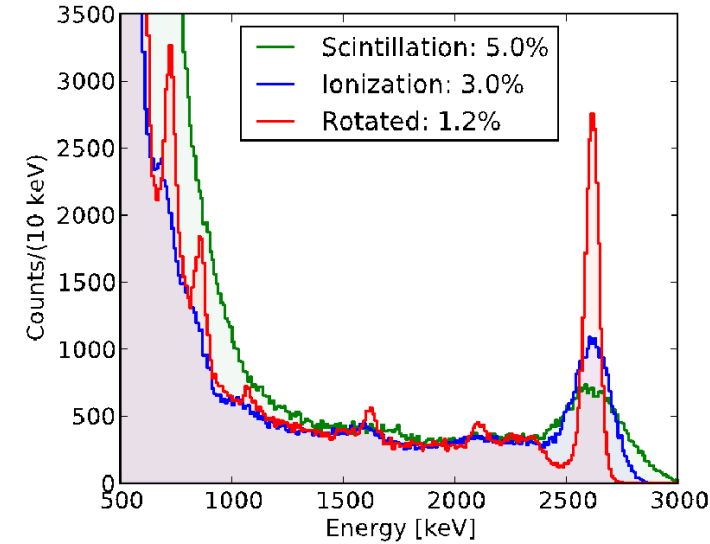
nEXO collaboration, 2022 J. Phys. G: Nucl. Part. Phys. 49 015104

Energy resolution

EXO-200 Th-228 source calibration data



Energy spectra of Th-228 events



Fractional resolution:
 $\leftarrow \frac{\sigma_E}{E}$

Rotated energy resolution is dominated by light collection efficiency



Light collection efficiency (ϵ)

Photon detection efficiency

$$\epsilon = PTE \times DAP = PTE \times \frac{PDE}{1-R}$$

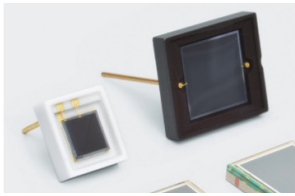
Photon transport efficiency

Device avalanche probability

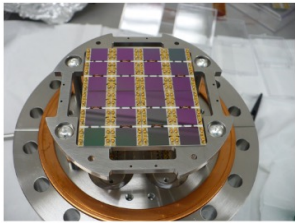
Reflection at normal incidence in vacuum

Light Collection

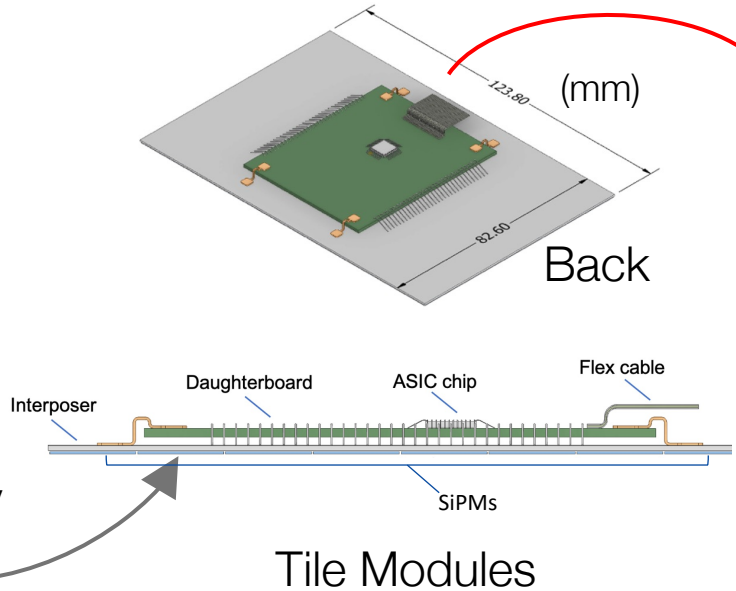
Photon detection system



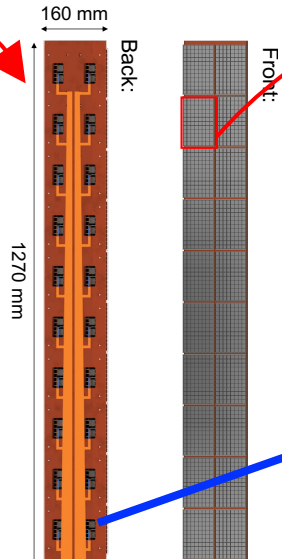
SiPMs



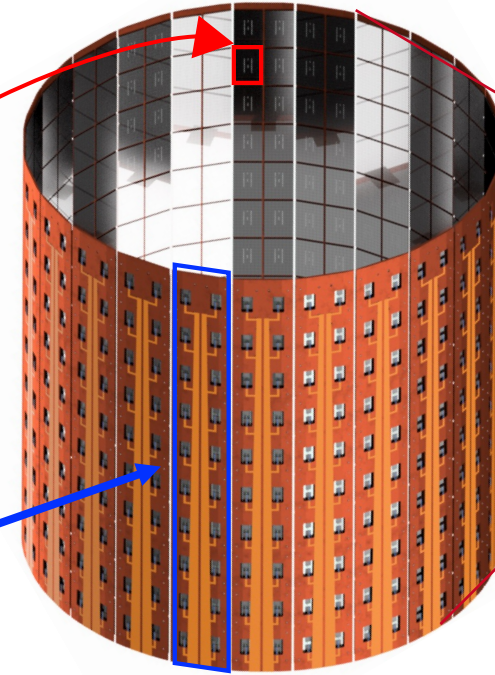
SiPM R&D array



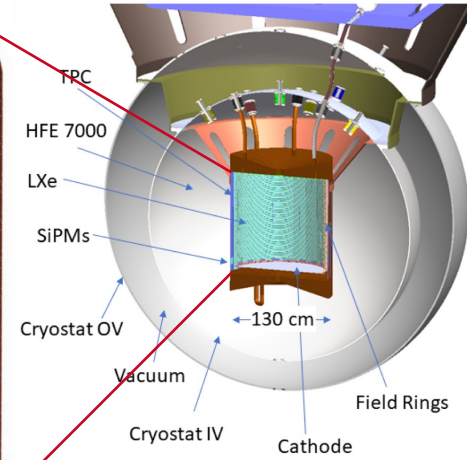
Tile Modules



SiPM staves



Full photon detection system



Silicon Photo-Multipliers (SiPMs)

Individual SiPMs

Grouped in 6 cm² sub-arrays → readout channels

Tile Modules

16 sub-arrays to tile w/ smaller daughterboard & integrated ASIC

20 tile modules arrayed to form stove

Staves

24 staves surround barrel, behind field shaping rings

Electroformed copper

Geometry

Square cylinder

Decreases the number of reflections before hitting a photodetector

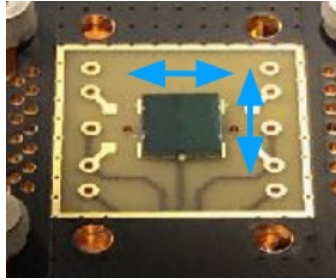
Photocoverage

4.6 m²

7,680 channels

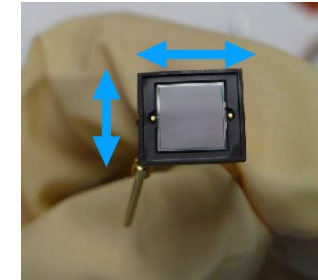
VUV-sensitive SiPMs in nEXO

FBK

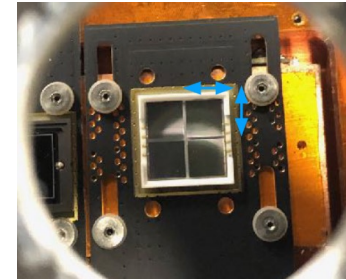


FBK VUVHD3

Hamamatsu



HPK VUV4-50



HPK VUV4-Q-50
Quad

2 candidate manufacturers

Fondazione Bruno Kessler (FBK)

Hamamatsu Photonics (HPK)

Tested 3 devices (6x6mm²)

Replaces
previous
generation:
FBK VUVHD1

G. Gallina, nEXO collaboration. Performance of novel VUV-sensitive Silicon Photo-Multipliers for nEXO. Eur. Phys. J. C 82, 1125 (2022)

nEXO requirements to meet $\leq 1.1\%$ energy resolution

Photon detection efficiency (PDE)	$\geq 15\%$ for 175 nm photons
Dark count rate at -100°C	$< 10 \text{ Hz/mm}^2$
Fluctuations in correlated avalanches (CAF) per pulse in $100\mu\text{s}$ at -100°C	< 0.4

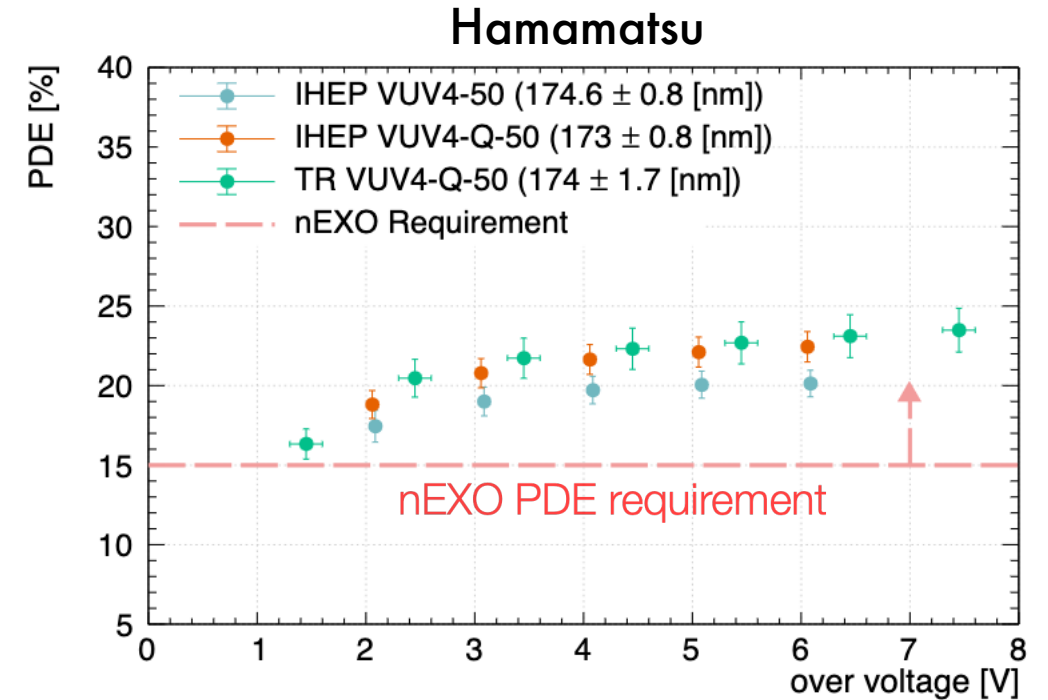
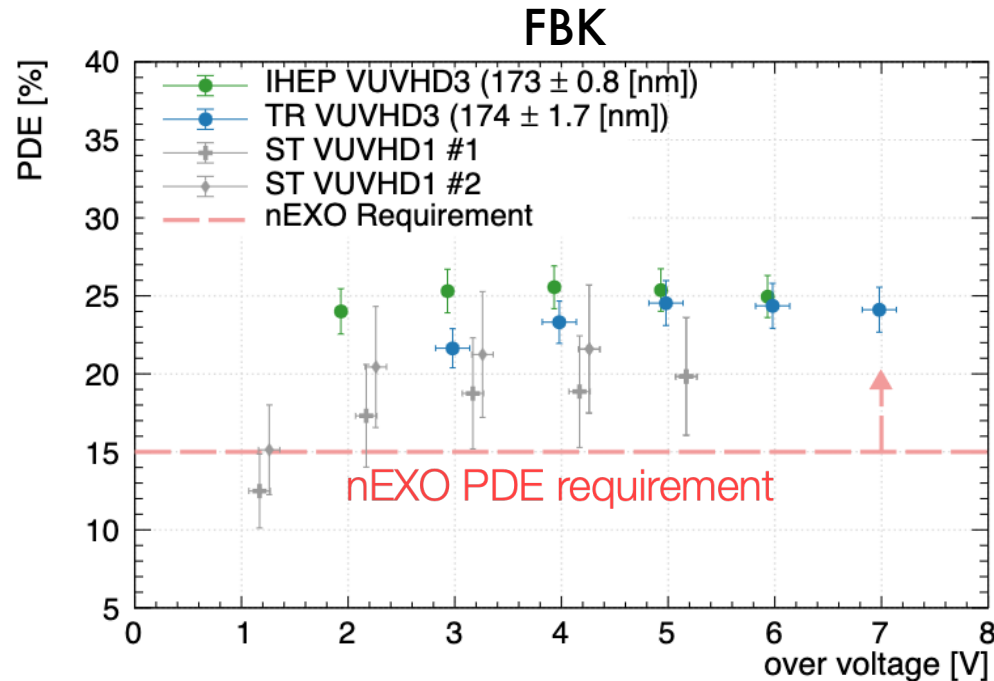
Photon detection efficiency (PDE)

Light collection efficiency (ϵ):

$$\epsilon = PTE * \frac{PDE}{1 - R}$$

175 nm PDE as function of over voltage

Requirement: $\geq 15\%$ for ~ 175 nm photons



Devices meet nEXO requirement from 1.5V over voltage!

TRIUMF: 165K
IHEP: 300K

Correlated avalanche fluctuations (CAF)

$$CAF = \frac{\sigma_{\Lambda}}{1 + \langle \Lambda \rangle}$$

RMS error of CA charge per photoelectron (PE)

Mean charge in CA per primary PE

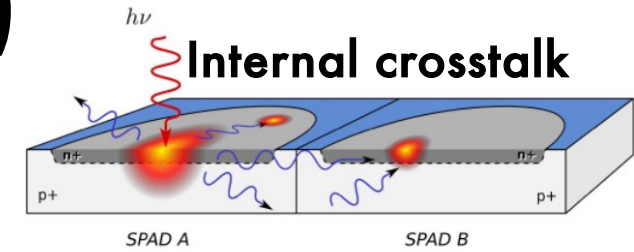
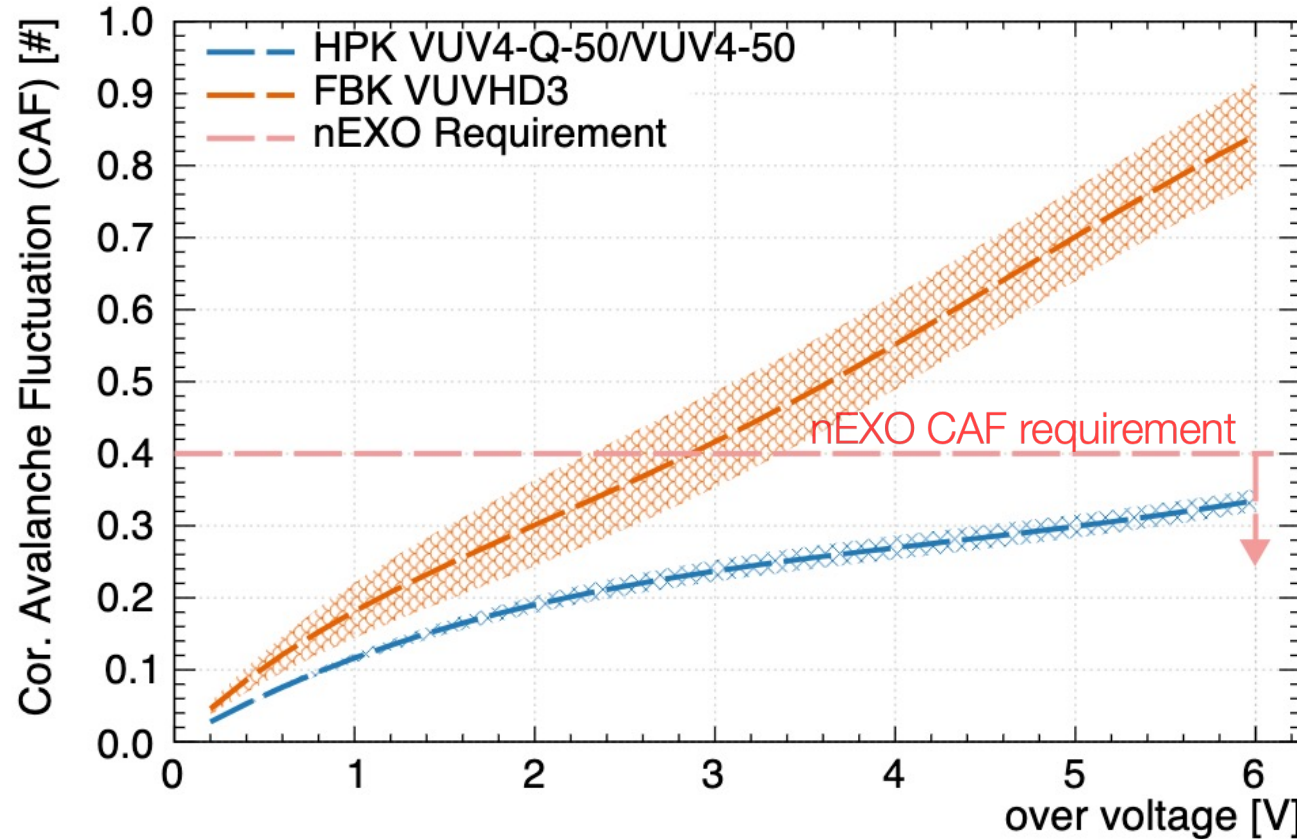


Image: I. Rech (2008)



Afterpulsing

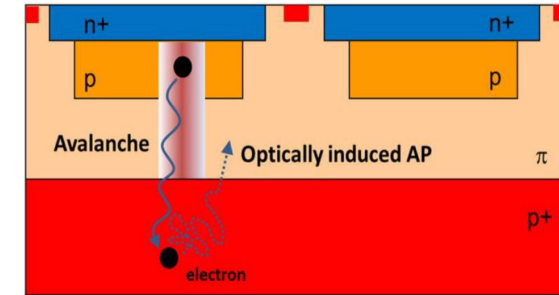


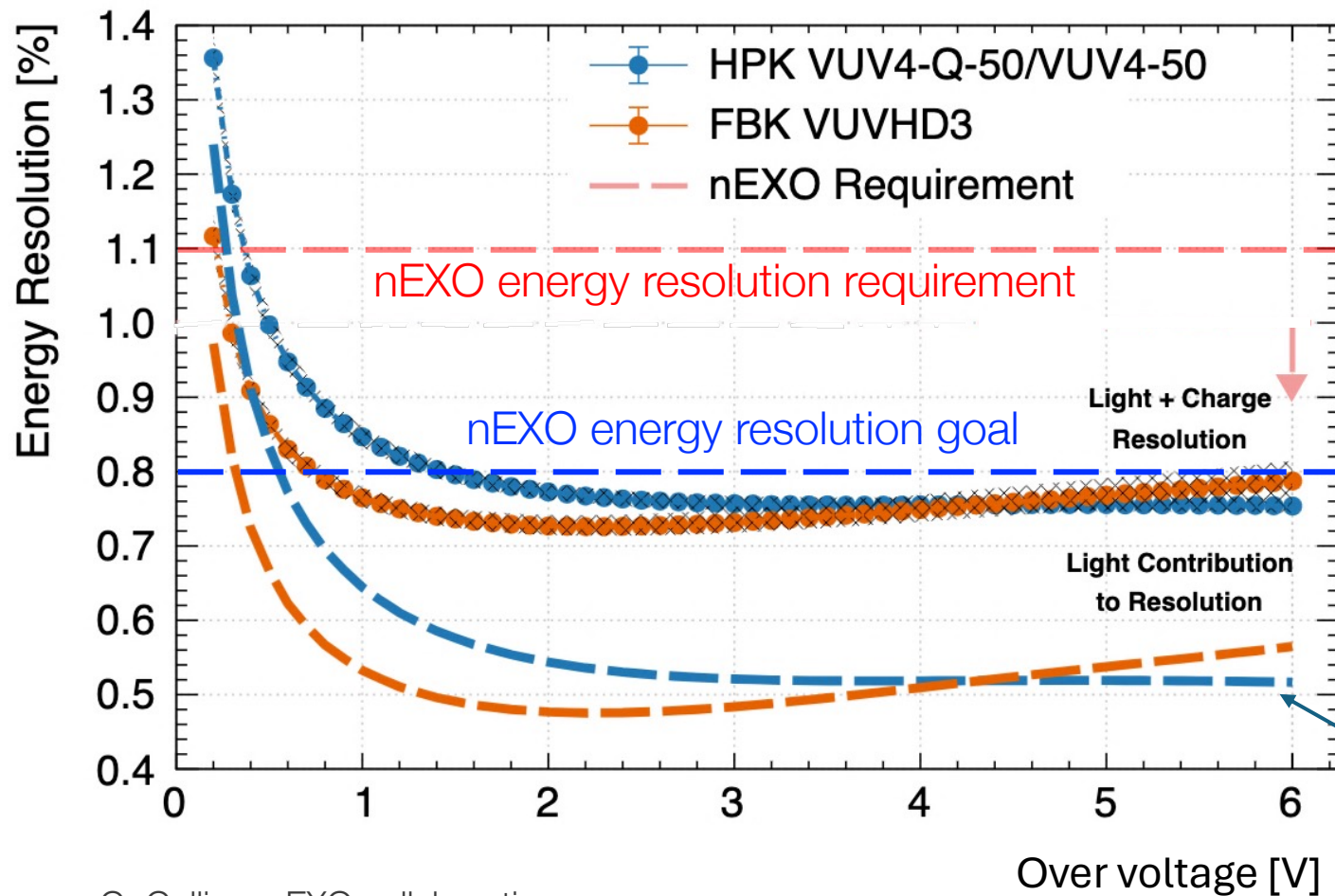
Image: C. Piemonte & A. Gola (2019)

Devices meet nEXO requirement at optimal over voltage

G. Gallina, nEXO collaboration.
Eur. Phys. J. C 82, 1125 (2022)

nEXO energy resolution with candidate SiPMs

Estimated energy resolution as a function of applied over voltage



G. Gallina, nEXO collaboration,
Eur. Phys. J. C 82, 1125 (2022)

Energy resolution
nEXO requirement $\leq 1.1\%$
nEXO goal $\leq 0.8\%$

Devices meet our requirements!

Note: Yet to account for external cross talk. Might produce slightly steeper rise but shouldn't impact reaching goal.

Papers from TRIUMF & IHEP out soon!

Contribution to light channel to total energy resolution neglecting recombination fluctuations

Optical Simulations

Chroma

GPU-accelerated ray tracing package

- Up to 300x faster than Geant4
- Can work with detailed geometry

Light collection efficiency (\mathcal{E}):

$$\mathcal{E} = \text{PTE} * \frac{PDE}{1 - R}$$



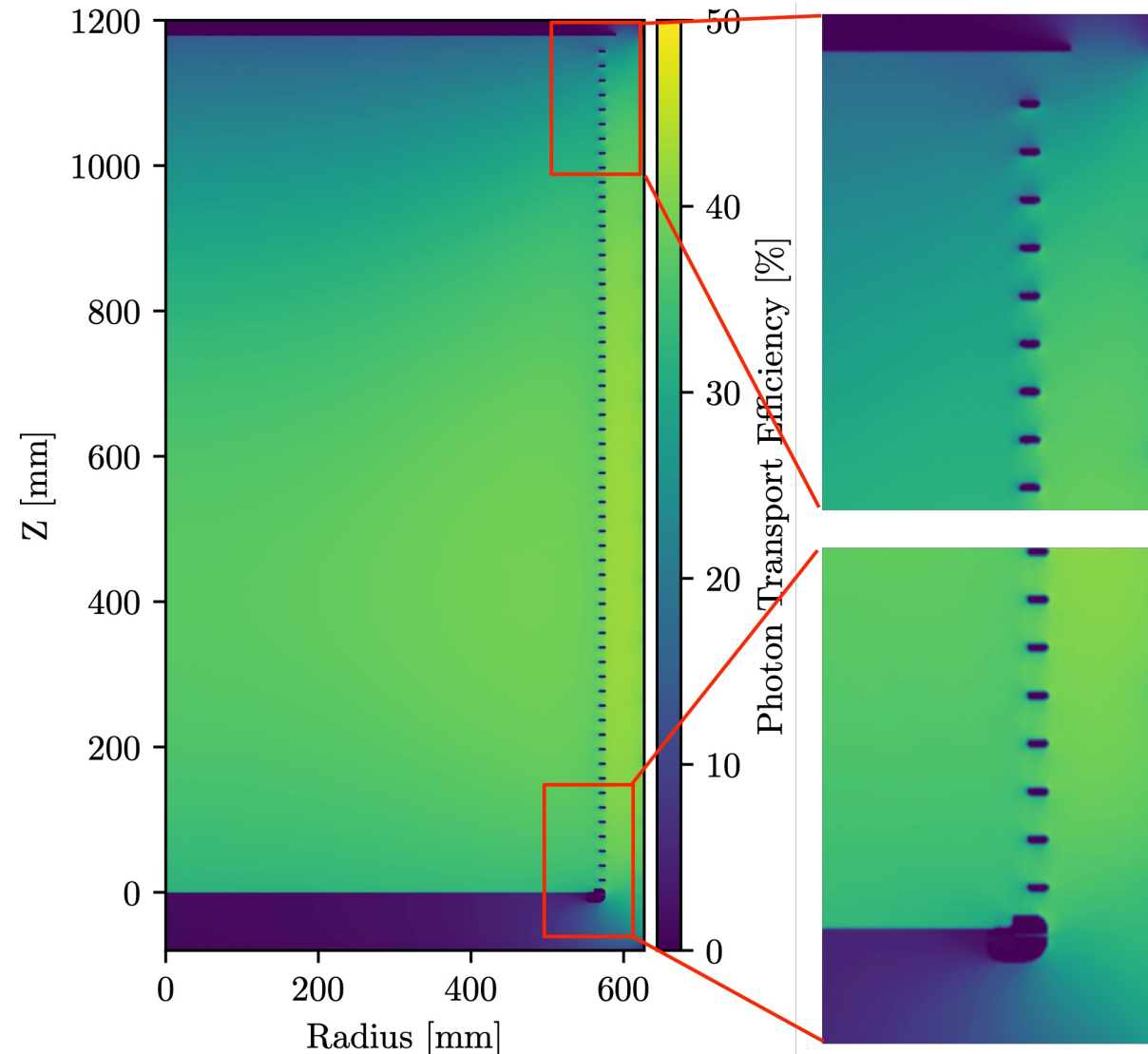
Photon transport efficiency (PTE)

Most detailed light response of nEXO

Contains ~1 trillion photons!

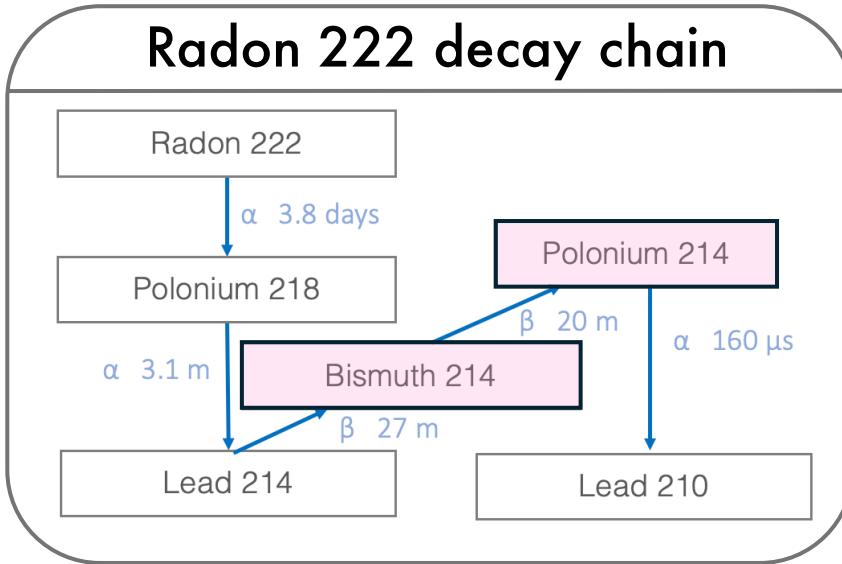
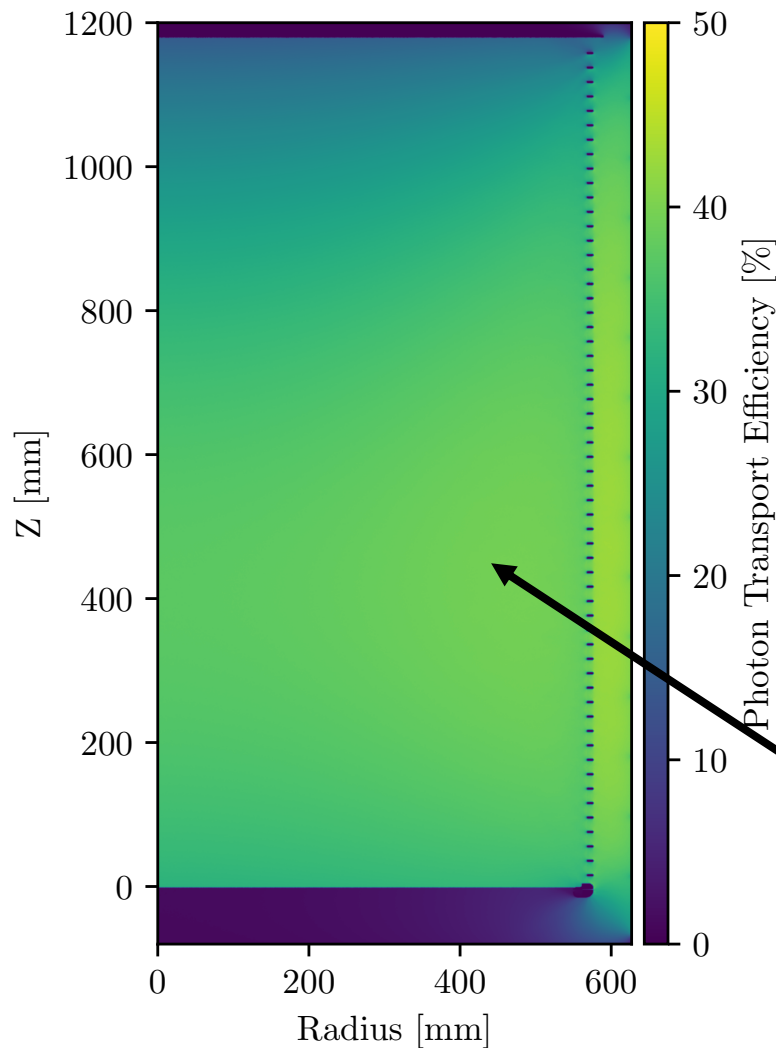
nEXO collaboration, 2022 J. Phys. G:
Nucl. Part. Phys. 49 015104

Lightmap from nEXO sensitivity paper



Light Map: Ako Jamil

Improving discrimination for Bi-Po tagging



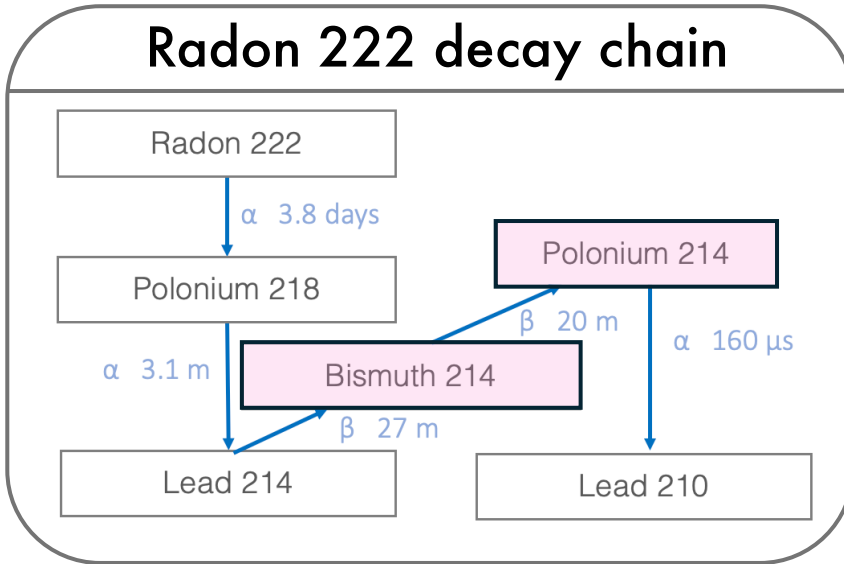
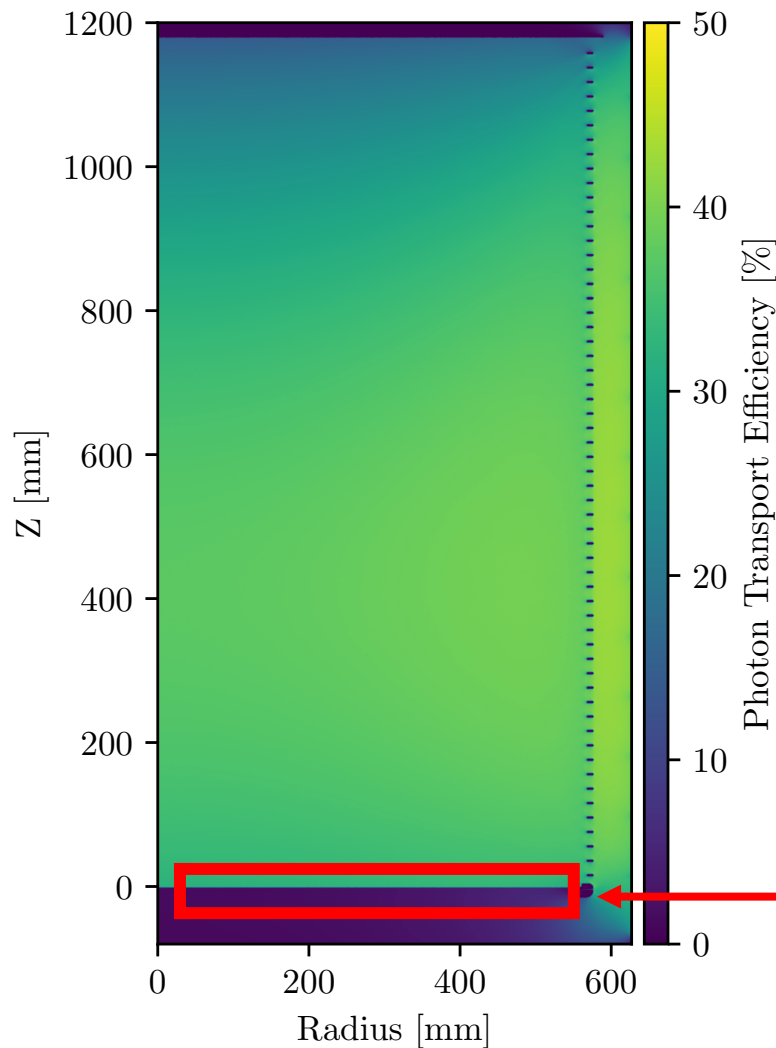
Backgrounds

Bi-214 is a dominant background with a gamma close to our 2.5 MeV Q-value

In the volume, we can reject this background with perfect efficiency by tagging Po-214 α

$T_{1/2}^{\alpha} = 160 \mu\text{s}$

Improving discrimination for Bi-Po tagging

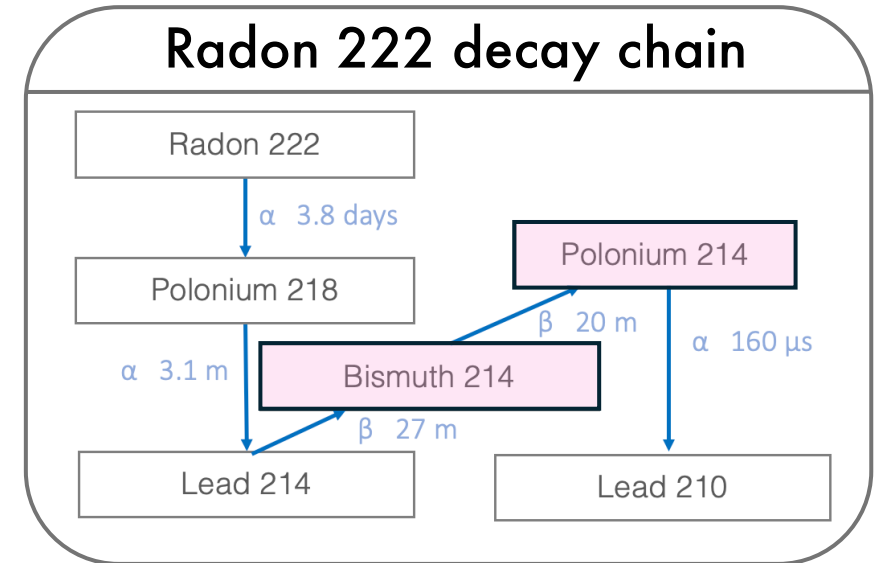
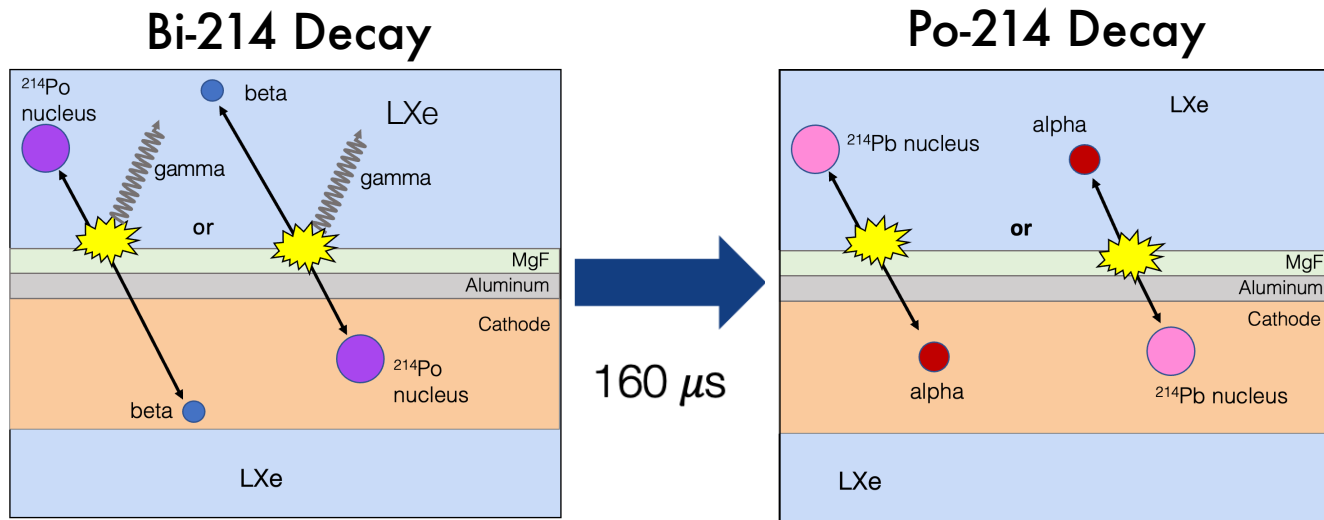
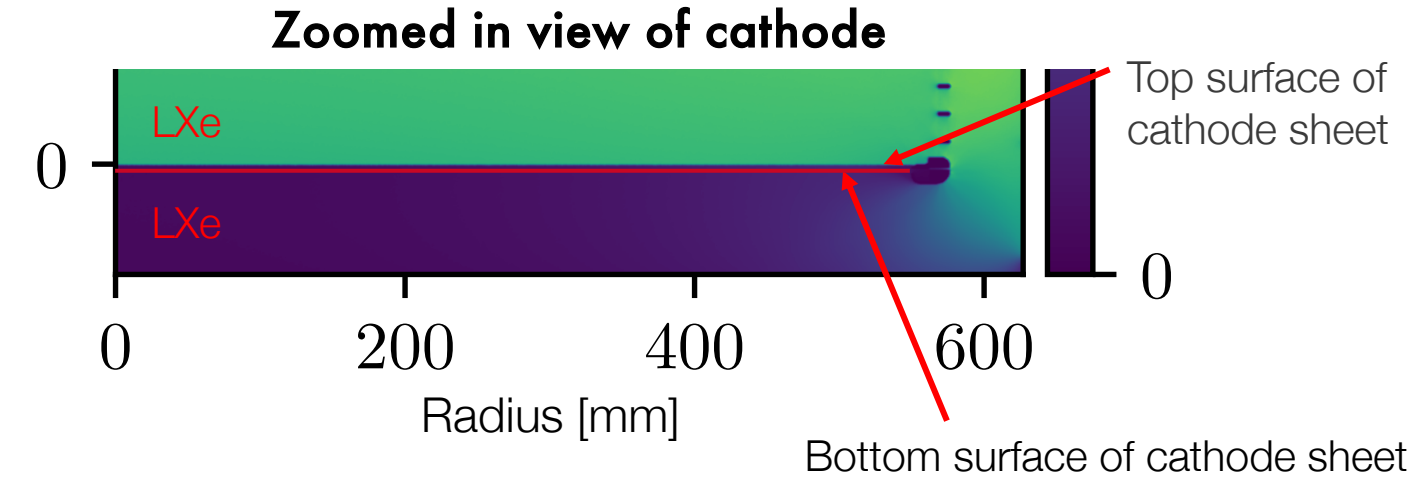


Backgrounds

Bi-214 is a dominant background with a gamma close to our 2.5 MeV Q-value

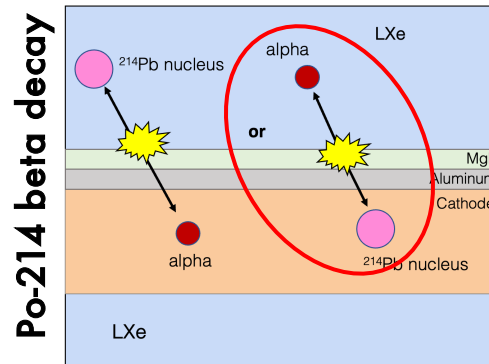
Rn-222 ionized daughters can plate out on cathode
 At edges like this, it is more difficult to tag Bi-Po events...

Improving discrimination for Bi-Po tagging



- Current sensitivity projection assumes no tagging based on spatial light discrimination

Alpha particle tagging above cathode



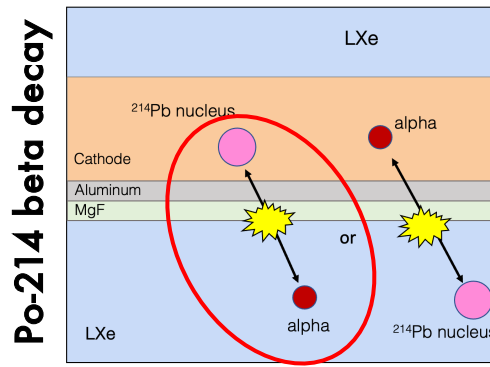
In the volume, we can reject this background with perfect efficiency by tagging Po-214 α

$$T_{1/2}^{\alpha} = 160 \mu\text{s}$$

Under cathode, current sensitivity projection assumes NO tagging

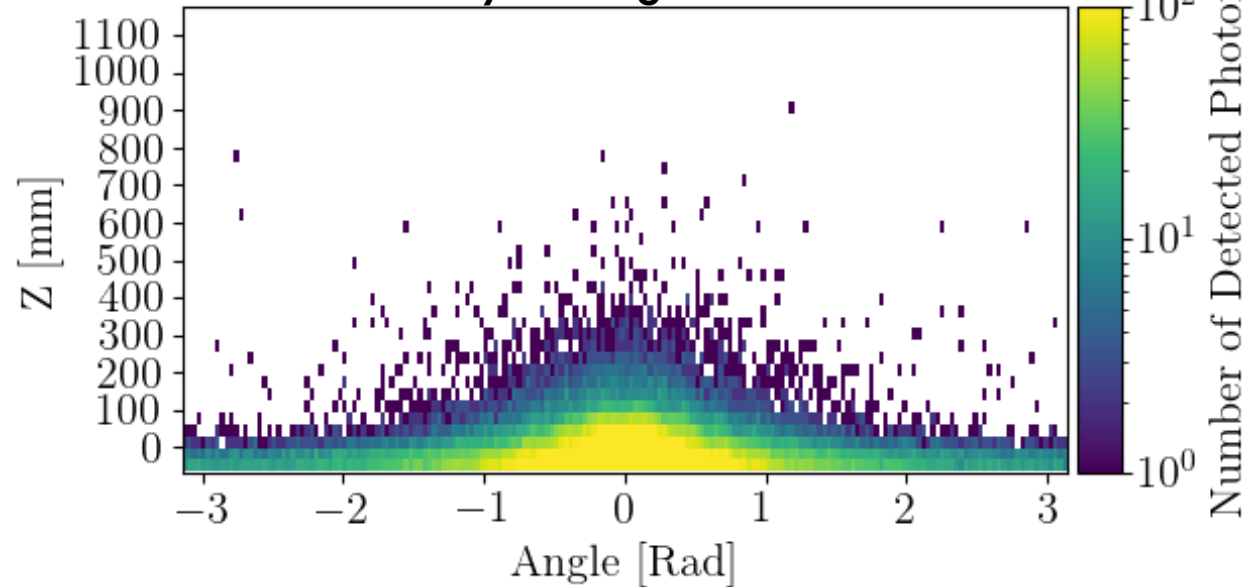
Alpha particle tagging below cathode

Hit pattern of Po-214 alpha decay below surface of cathode

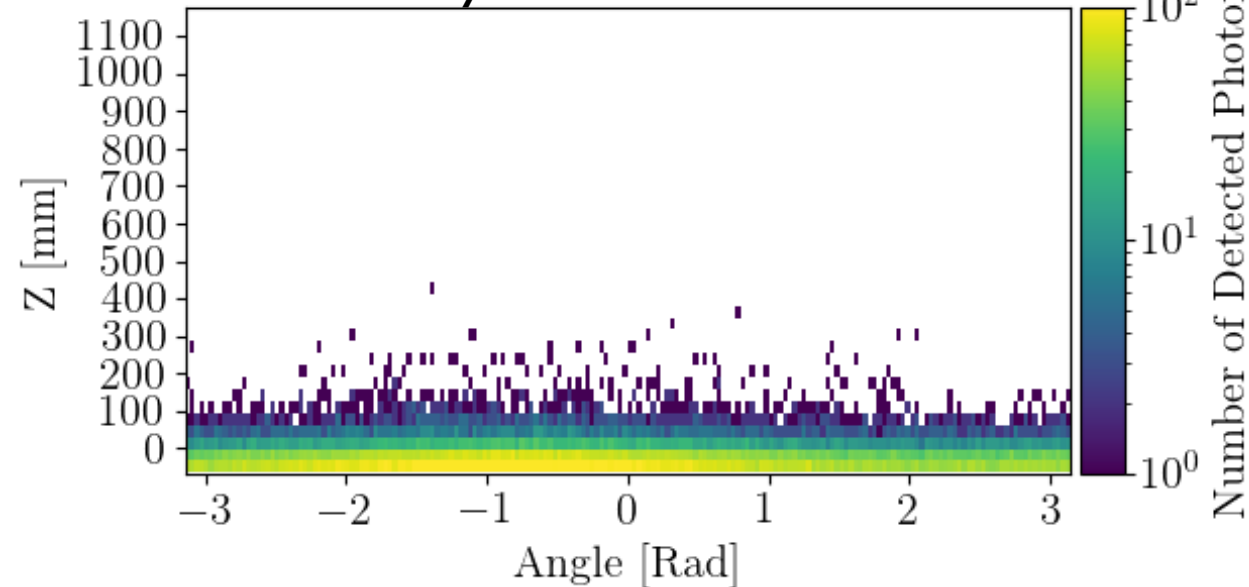


In the volume, we can reject this background with perfect efficiency by tagging Po-214 α
 $T_{1/2}^\alpha = 160 \mu\text{s}$
 Under cathode, current sensitivity projection assumes NO tagging

Decay at edge of detector



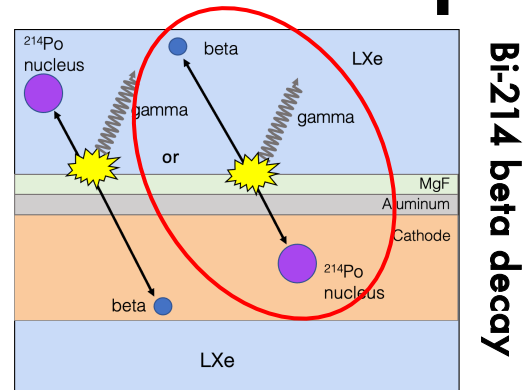
Decay at center of detector



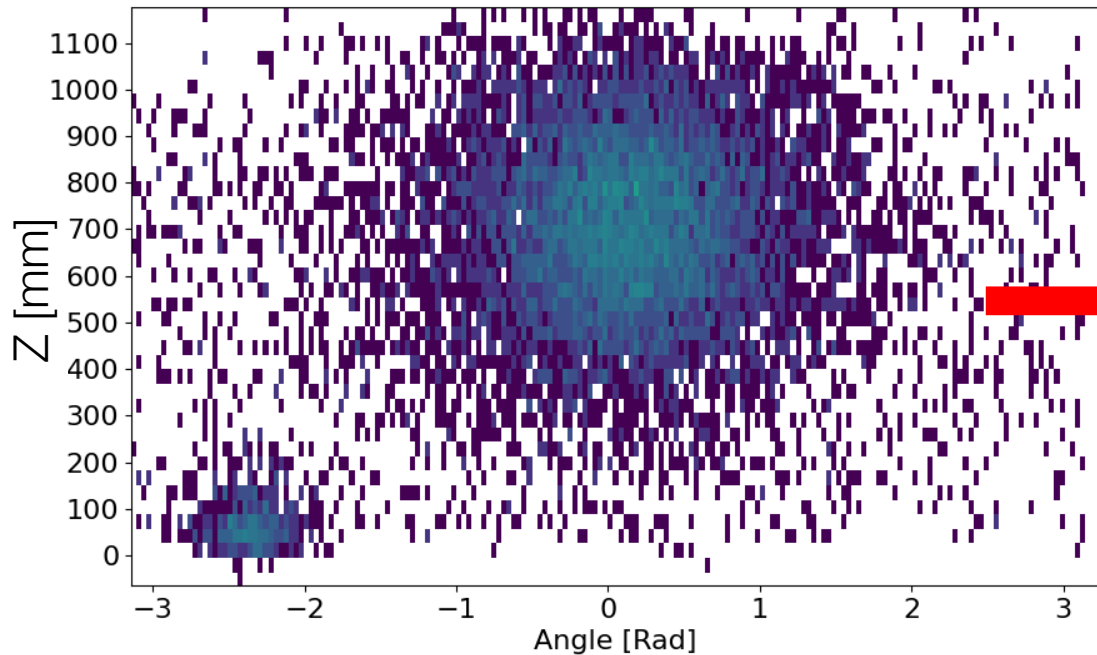
We can tag these alphas based on spatial light discrimination!

Topological discrimination with hit patterns

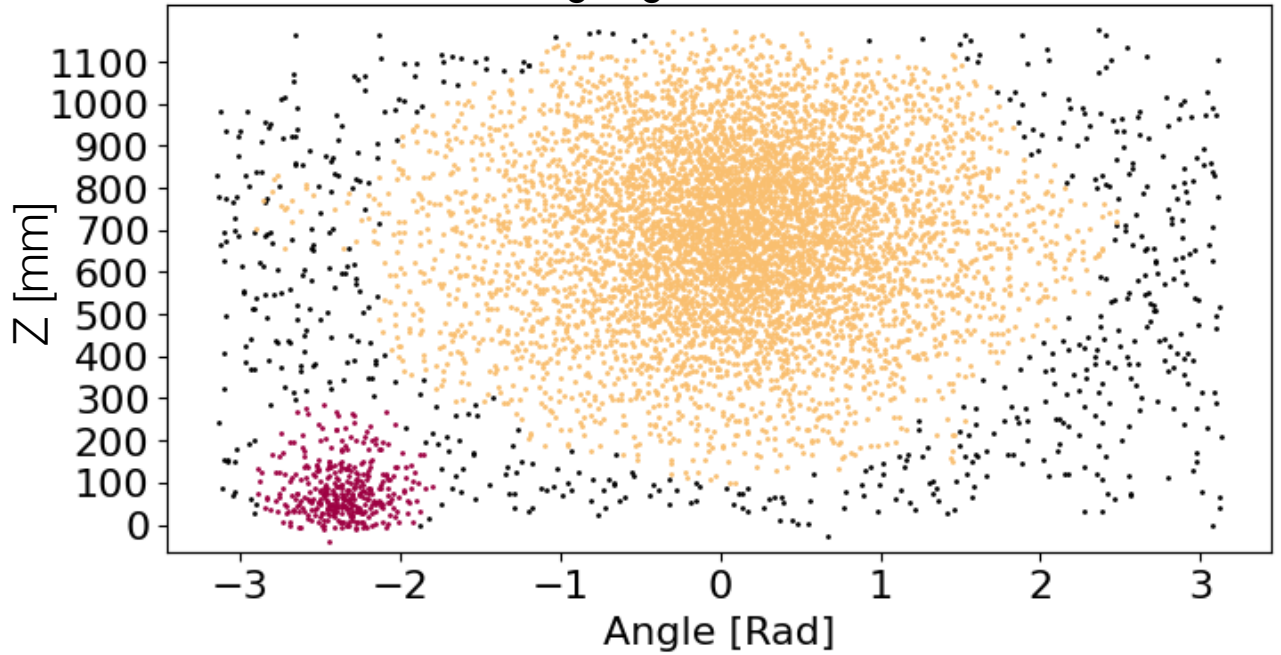
Hit pattern of Bi-214 beta decay above surface of cathode



Beta + Gamma Hit Pattern 5



Clustering algorithm on Hit Pattern 5



Current work: Exploring clustering algorithm to discriminate between background and signal
 Future work: Employ Convolutional Neural Network

Summary

Light detection

Have devices from two manufacturers that meet nEXO requirements!!

- Good agreement amongst multiple institutions
 - More measurements than shown today

G. Gallina, nEXO collaboration. Performance of novel VUV-sensitive Silicon Photo-Multipliers for nEXO. Eur. Phys. J. C 82, 1125 (2022)
arXiv:2209.07765

Optical simulations

Provide better background rejections and better modeling for energy resolution

- Ongoing discrimination work to better characterize events

Thank you!! Questions?



International collaboration involving
10 countries, 36 institutions, ~200
collaborators

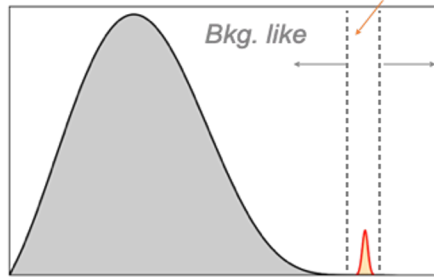


This material is based upon work supported by the National Science Foundation Graduate Research Fellowship.

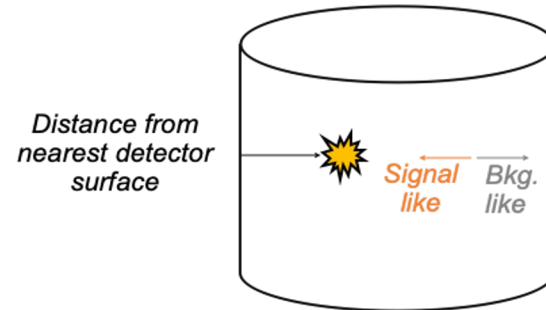
Back-up slides

Multiparameter analysis

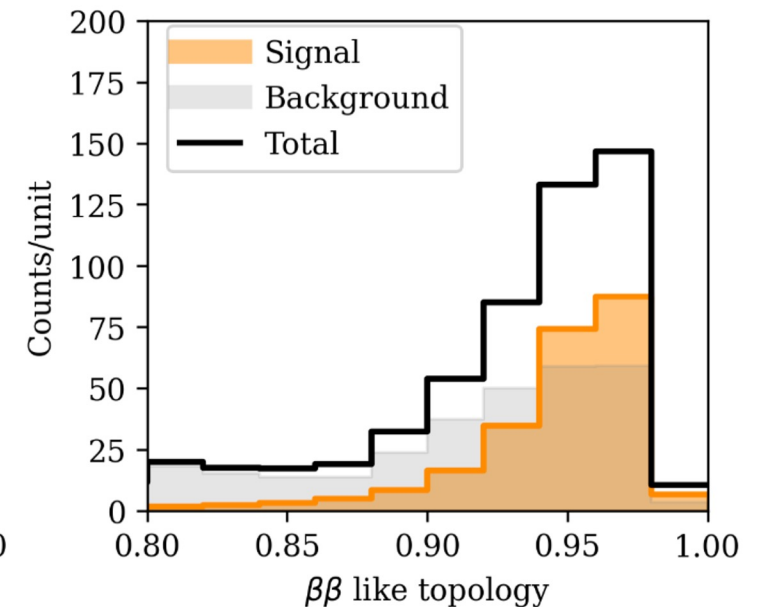
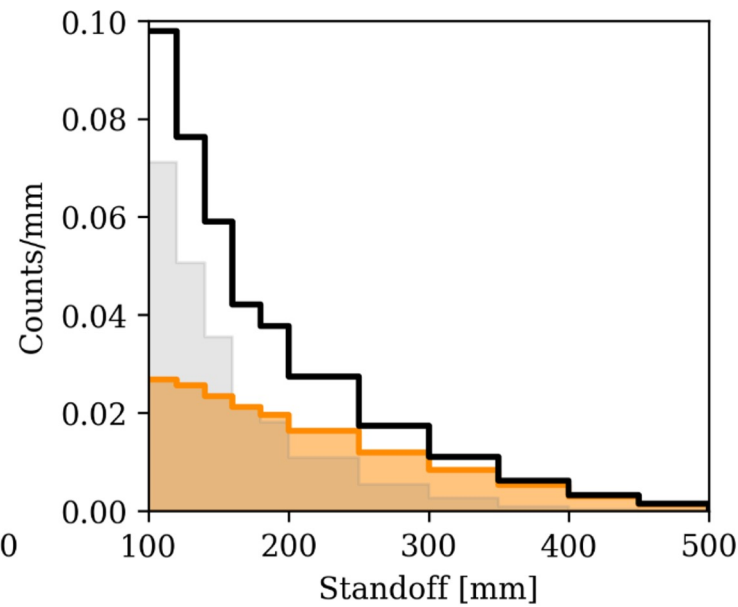
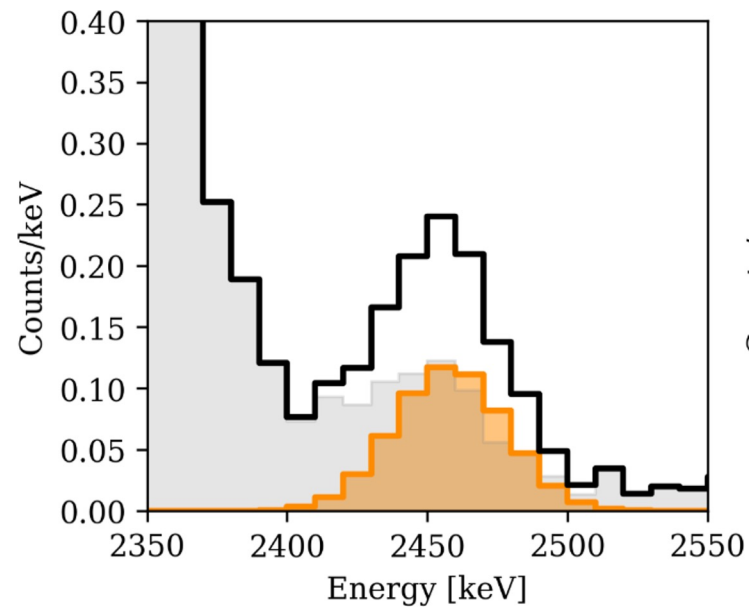
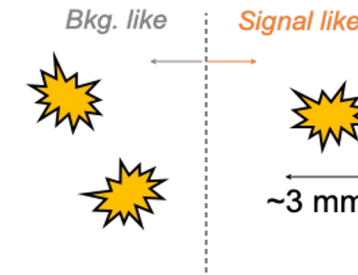
Energy: *Signal like*



Standoff:



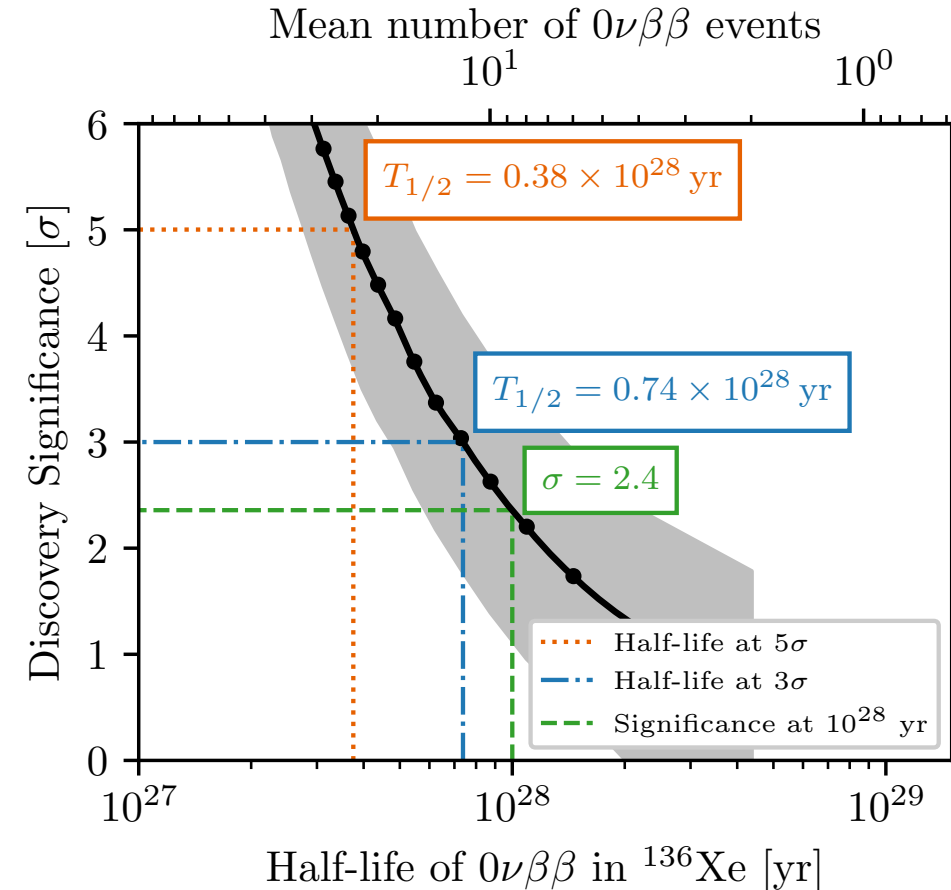
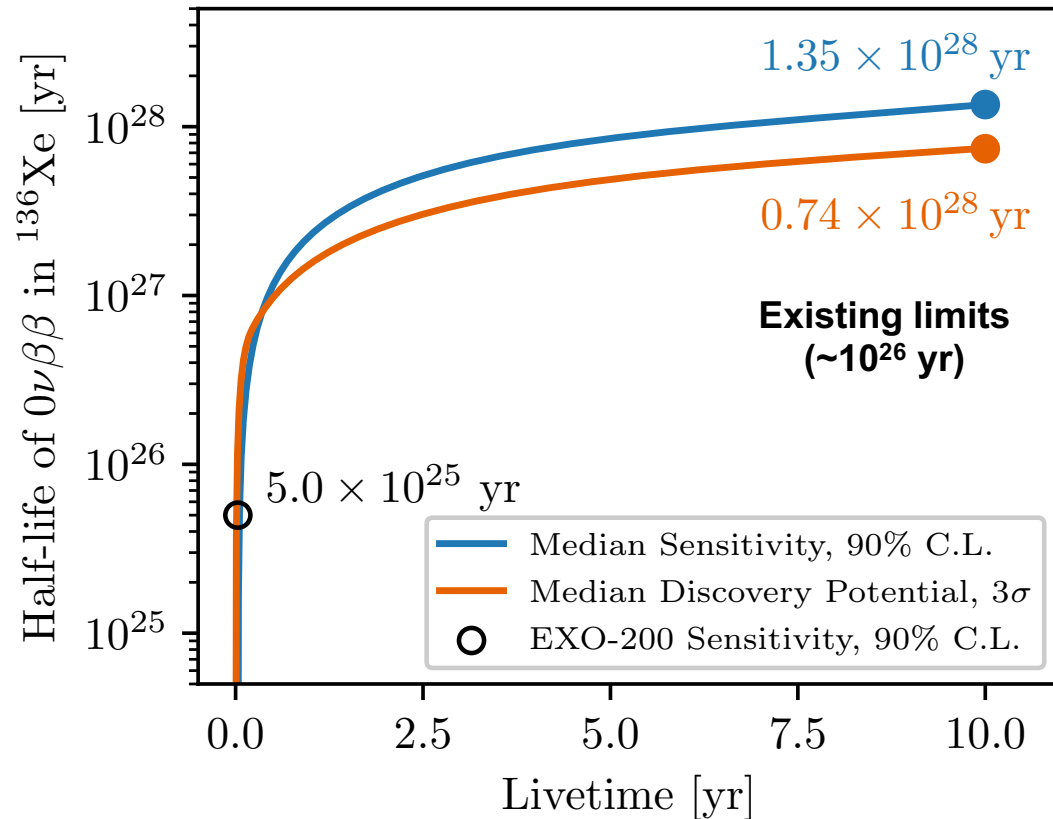
Topology:



nEXO collaboration, 2022 J. Phys. G: Nucl. Part. Phys. 49 015104

Sensitivity and discovery potential

- Projected half-life: 1.35×10^{28} years at 90% confidence level
- Design goal $\leq 1\%$ energy resolution at Q-value of 2458 keV



nEXO collaboration, 2022 J. Phys. G: Nucl. Part. Phys. 49 015104

Hardware setups

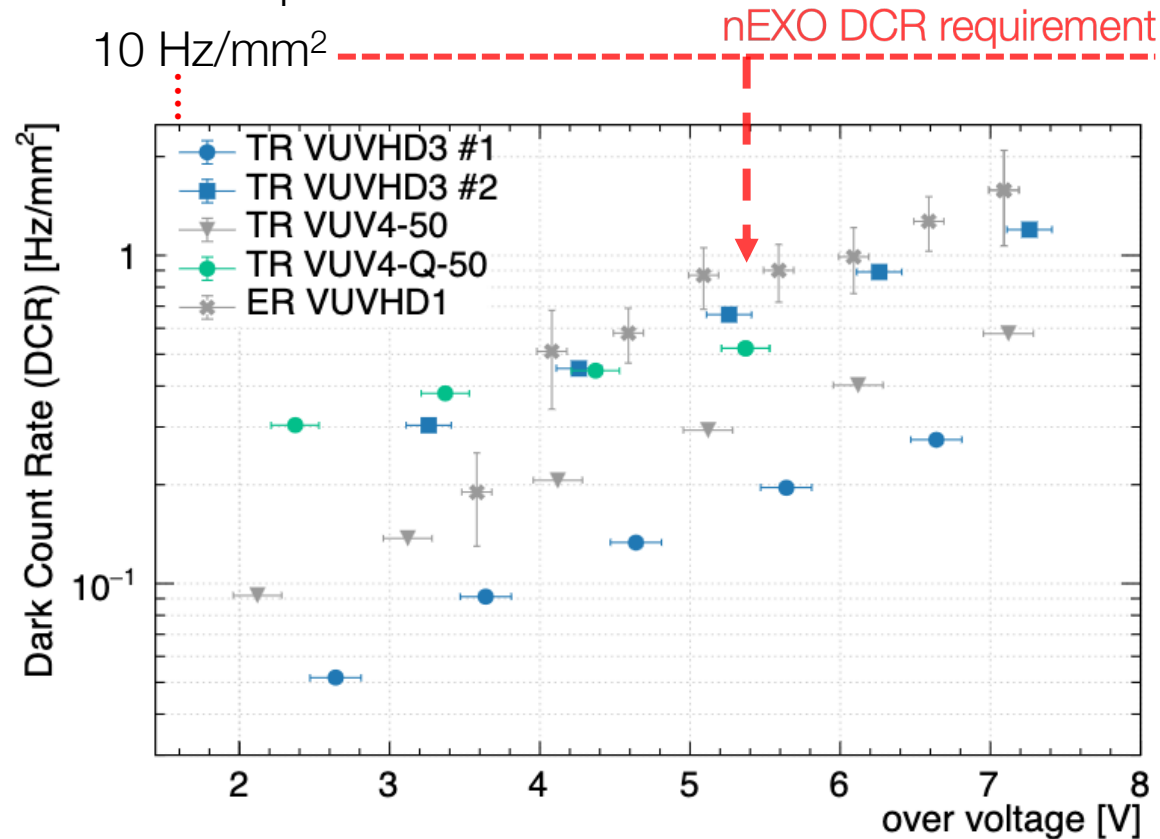
SiPM characterization - combined effort of multiple institutions

	TRIUMF	McGill University	Yale University	University of Massachusetts, Amherst	Brookhaven National Laboratory [28]	Institute of High Energy Physics
Abbreviation	TR	MG	YALE	UMASS	BNL	IHEP
Temperature Stabilisation	Instec MK2000	Lakeshore 350	custom LabVIEW	custom LabVIEW	CryoCon 24C	CTE-SG12012-02W
Measurement Temperature	163 K	163 K	163 K	190 K/163 K	163 K	300 K/233 K
SiPM Amplification	MAR6-SM+ OPA695 [29]	MAR6-SM+ OPA695 [29]	CR-113-R2 SRS SR-560	CR-113-R2 CR-200-100ns	MAR6-SM+ OPA695 [29]	custom amplifier [20]
DAQ pulse counting	CAEN DT5730B	Rohde & Schwarz RTO2024	Rohde & Schwarz RTB2004	Teradyne ZTEC ZT4421	MSO64 Tektronix	CAEN DT5751
DAQ I-V	Keithley 6487 Keysight B2985A	Keysight B2987	Keithley 6487	Keithley 6482	-	Keithley 6487
LXe/GXe	No	No	Yes	Yes	No	No
SiPM Noise analysis	Yes	Yes	Yes	Yes	Yes	Yes
SiPM PDE	Yes	No	No	No	No	Yes

G. Gallina, nEXO collaboration.
Eur. Phys. J. C 82, 1125 (2022)

Dark count rate (DCR)

Geiger mode avalanche in absence of a photon



Requirement at 163 K ≤ 10 Hz/mm²

Requirement met for all devices in the entire range of over voltages!

G. Gallina, nEXO collaboration.
Eur. Phys. J. C 82, 1125 (2022)

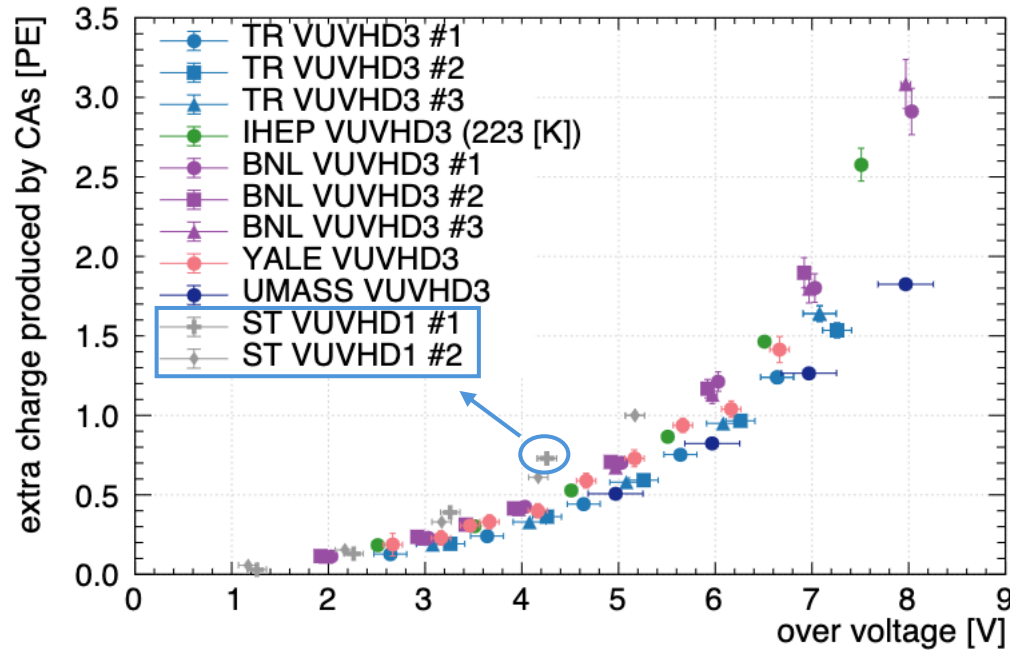
G. Gallina et al. Performance of novel VUV-sensitive Silicon Photo-Multipliers for nEXO. Eur. Phys. J. C 82, 1125 (2022)

Correlated avalanches (CA) FBK VUVHD3

$$CAF = \frac{\sigma_{\Lambda}}{1 + \langle \Lambda \rangle}$$

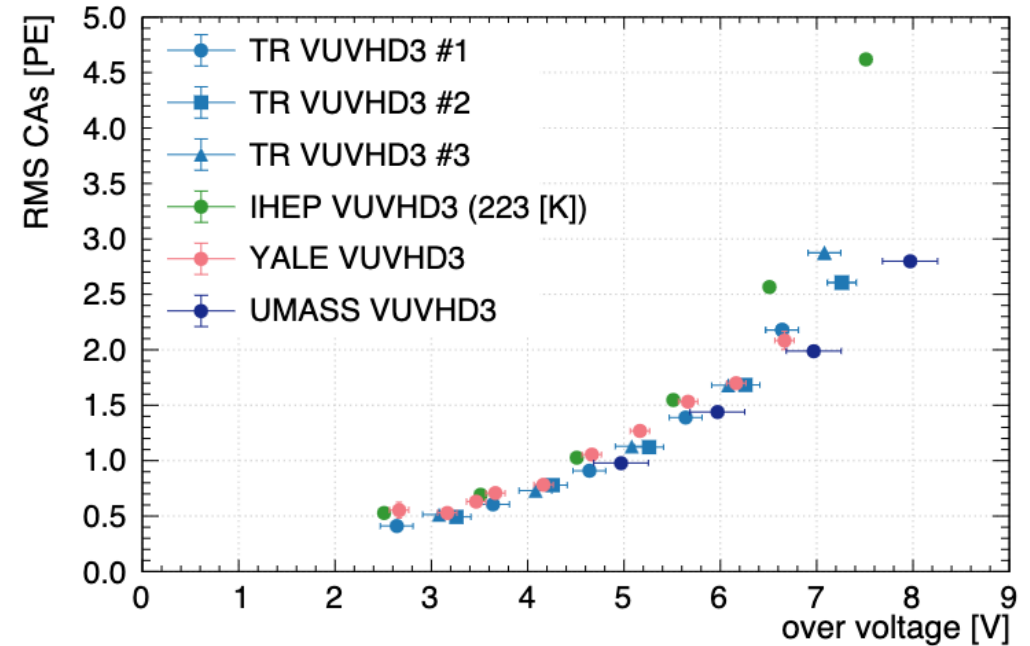
σ_{Λ} ← RMS error of CA charge per photoelectron (PE)
 $\langle \Lambda \rangle$ ← Mean charge in CA per primary PE

Avg extra charge produced by CA (Λ) as a function of applied over voltage



Grey points are FBK VUVHD1*
New VUVHD3 are an improvement!

RMS error (σ_{Λ}) as function of over voltage



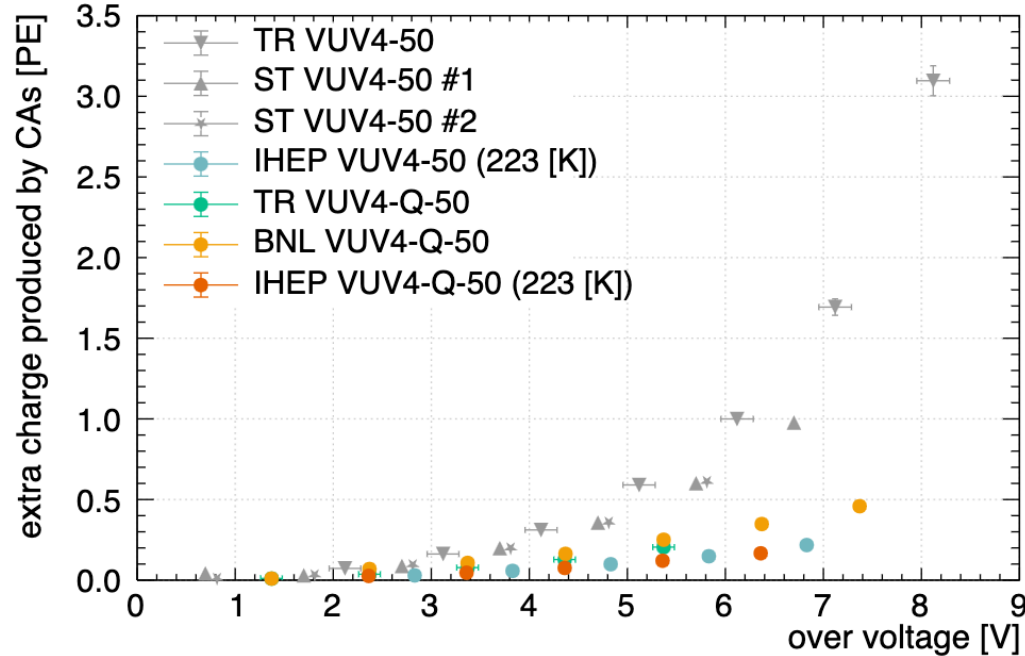
G. Gallina, nEXO collaboration.
Eur. Phys. J. C 82, 1125 (2022)

* A. Jamil et al, IEEE TNS 65 (2018)

Correlated avalanches (CA)

HPK VUV4s

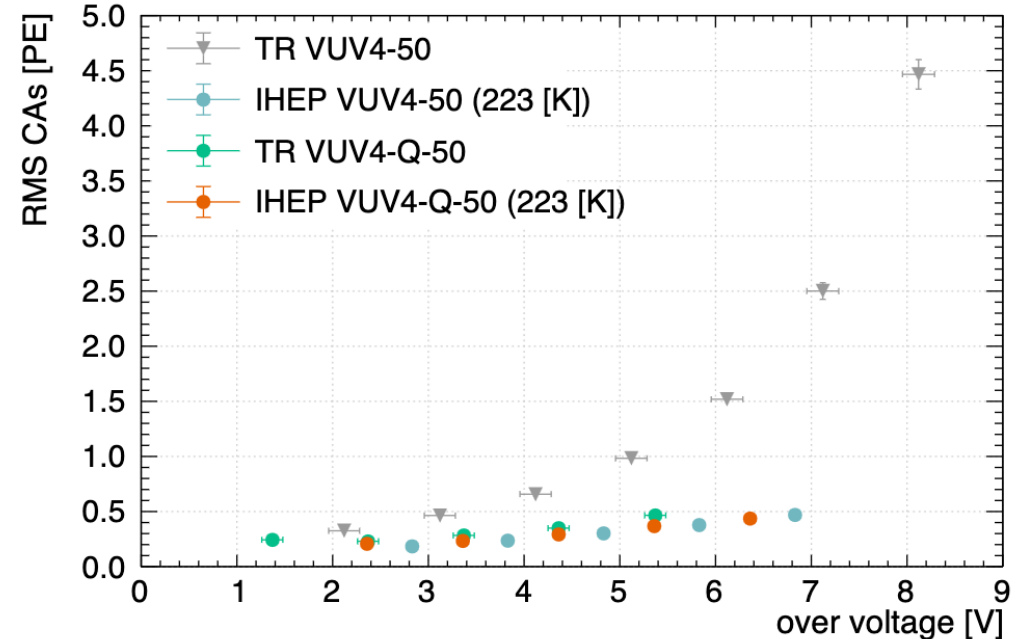
Avg extra charge produced by CA (Λ) as a function of applied over voltage



$$CAF = \frac{\sigma_{\Lambda}}{1 + \langle \Lambda \rangle}$$

σ_{Λ} ← RMS error of CA charge per photoelectron (PE)
 $\langle \Lambda \rangle$ ← Mean charge in CA per primary PE

RMS error (σ_{Λ}) as function of over voltage



G. Gallina, nEXO collaboration.
Eur. Phys. J. C 82, 1125 (2022)

Grey points are older test

HPK VUV4 has almost no correlated avalanches!